

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (Canceled).

26. (Currently amended) ~~A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said~~ plasma etching composition consisting essentially of:

~~a flowing plasma etchant mixture consisting of at least one fluorocarbon~~ two fluorocarbons[[,]] and ammonia, wherein said at least ~~one fluorocarbon~~ two fluorocarbons[[,]] and said ammonia form a reactive mixture.

27. (Currently amended) The composition of claim 26, wherein said ~~fluorocarbon is at least one member~~ at least two fluorocarbons are selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (Currently amended) The composition of claim 27, wherein said ~~fluorocarbon is at least one member~~ at least two fluorocarbons are selected from the group consisting of C₄F₈, C₄F₆, C₅F₈, CF₄, C₂F₆, C₃F₈, CHF₃, and CH₂F₂.

29. (Currently amended) The composition of claim 26, wherein said ~~fluorocarbon is at least one member~~ at least two fluorocarbons are selected from the group consisting of CF₄, CHF₃, and CH₂F₂.

30. (Canceled).

31. (Currently amended) The composition of claim ~~[[30]]~~ 28, wherein said ~~fluorocarbon is~~ at least two fluorocarbons are a combination of CF_4 , CHF_3 , and CH_2F_2 .

Claims 32-70 (Canceled).

71. (Currently amended) A ~~composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said~~ plasma etching composition consisting essentially of:

~~a plasma etchant mixture consisting of~~ CF_4 , at least one other fluorocarbon~~[[,]]~~ and NH_3 , wherein said CF_4 , said at least one other fluorocarbon, and said NH_3 form a reactive mixture.

Claims 72-76 (Canceled).

77. (Currently amended) A ~~composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said~~ plasma etching composition consisting essentially of:

~~a gaseous etchant mixture consisting of~~ at least one fluorocarbon, at least one additional gas selected from the group consisting of oxygen and nitrogen, and ammonia, wherein said at least one fluorocarbon, said at least one additional gas, and said ammonia form a reactive mixture.